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1     ABSTRACT OF THE DISCLOSURE

          A semiconductor device includes a substrate,  
a gate oxide film formed on the substrate, a gate  
electrode provided on the gate oxide film, first and  
5     second diffusion regions formed in the substrate at  
both lateral sides of the gate electrode. The gate  
electrode includes a first region located immediately  
underneath the gate electrode and a second region  
adjacent to the first region, wherein the first and  
10    second regions contain N atoms with respective  
concentrations such that the second region contains N  
with a higher concentration as compared with the first  
region.

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